

勝特力材料 886-3-5753170  
 勝特力电子(上海) 86-21-54151736  
 勝特力电子(深圳) 86-755-83298787  
 Http://www.100y.com.tw

International  
**IR** Rectifier

**SMPS MOSFET**

PD- 93805B

IRFB31N20D

IRFS31N20D

IRFSL31N20D

HEXFET® Power MOSFET

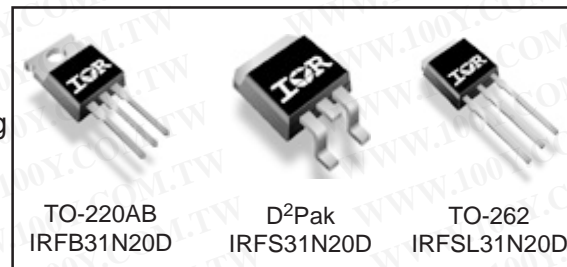
**Applications**

- High frequency DC-DC converters

V <sub>DSS</sub>	R <sub>DS(on)</sub> max	I <sub>D</sub>
200V	0.082Ω	31A

**Benefits**

- Low Gate-to-Drain Charge to Reduce Switching Losses
- Fully Characterized Capacitance Including Effective C<sub>oss</sub> to Simplify Design, (See App. Note AN1001)
- Fully Characterized Avalanche Voltage and Current



**Absolute Maximum Ratings**

	Parameter	Max.	Units
I <sub>D</sub> @ T <sub>C</sub> = 25°C	Continuous Drain Current, V <sub>GS</sub> @ 10V	31	A
I <sub>D</sub> @ T <sub>C</sub> = 100°C	Continuous Drain Current, V <sub>GS</sub> @ 10V	21	
I <sub>DM</sub>	Pulsed Drain Current ①	124	
P <sub>D</sub> @ T <sub>A</sub> = 25°C	Power Dissipation ②	3.1	W
P <sub>D</sub> @ T <sub>C</sub> = 25°C	Power Dissipation	200	
	Linear Derating Factor	1.3	W/°C
V <sub>GS</sub>	Gate-to-Source Voltage	± 30	V
dv/dt	Peak Diode Recovery dv/dt ③	2.1	V/ns
T <sub>J</sub>	Operating Junction and	-55 to + 175	°C
T <sub>STG</sub>	Storage Temperature Range		
	Soldering Temperature, for 10 seconds	300 (1.6mm from case )	
	Mounting torque, 6-32 or M3 screw④	10 lbf•in (1.1N•m)	

**Typical SMPS Topologies**

- Telecom 48V Input Forward Converters

Notes ① through ④ are on page 11

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# IRFB/IRFS/IRFSL31N20D

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Static @  $T_J = 25^\circ\text{C}$  (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	200	—	—	V	$V_{GS} = 0V, I_D = 250\mu A$
$\Delta V_{(BR)DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	—	0.25	—	V/°C	Reference to $25^\circ\text{C}, I_D = 1\text{mA}$
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	—	—	0.082	$\Omega$	$V_{GS} = 10V, I_D = 18A$ ④
$V_{GS(th)}$	Gate Threshold Voltage	3.0	—	5.5	V	$V_{DS} = V_{GS}, I_D = 250\mu A$
$I_{DSS}$	Drain-to-Source Leakage Current	—	—	25	$\mu A$	$V_{DS} = 200V, V_{GS} = 0V$
		—	—	250		$V_{DS} = 160V, V_{GS} = 0V, T_J = 150^\circ\text{C}$
$I_{GSS}$	Gate-to-Source Forward Leakage	—	—	100	nA	$V_{GS} = 30V$
	Gate-to-Source Reverse Leakage	—	—	-100		$V_{GS} = -30V$

Dynamic @  $T_J = 25^\circ\text{C}$  (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
$g_{fs}$	Forward Transconductance	17	—	—	S	$V_{DS} = 50V, I_D = 18A$
$Q_g$	Total Gate Charge	—	70	110	nC	$I_D = 18A$
$Q_{gs}$	Gate-to-Source Charge	—	18	27		$V_{DS} = 160V$
$Q_{gd}$	Gate-to-Drain ("Miller") Charge	—	33	49	ns	$V_{GS} = 10V, \text{④}$
$t_{d(on)}$	Turn-On Delay Time	—	16	—		$V_{DD} = 100V$
$t_r$	Rise Time	—	38	—		$I_D = 18A$
$t_{d(off)}$	Turn-Off Delay Time	—	26	—		$R_G = 2.5\Omega$
$t_f$	Fall Time	—	10	—		$R_D = 5.4\Omega$ ④
$C_{iss}$	Input Capacitance	—	2370	—		pF
$C_{oss}$	Output Capacitance	—	390	—	$V_{DS} = 25V$	
$C_{rss}$	Reverse Transfer Capacitance	—	78	—	$f = 1.0\text{MHz}$	
$C_{oss}$	Output Capacitance	—	2860	—	$V_{GS} = 0V, V_{DS} = 1.0V, f = 1.0\text{MHz}$	
$C_{oss}$	Output Capacitance	—	150	—	$V_{GS} = 0V, V_{DS} = 160V, f = 1.0\text{MHz}$	
$C_{oss\text{ eff.}}$	Effective Output Capacitance	—	170	—	$V_{GS} = 0V, V_{DS} = 0V \text{ to } 160V$ ⑤	

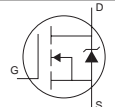
## Avalanche Characteristics

	Parameter	Typ.	Max.	Units
$E_{AS}$	Single Pulse Avalanche Energy②	—	420	mJ
$I_{AR}$	Avalanche Current①	—	18	A
$E_{AR}$	Repetitive Avalanche Energy①	—	20	mJ

## Thermal Resistance

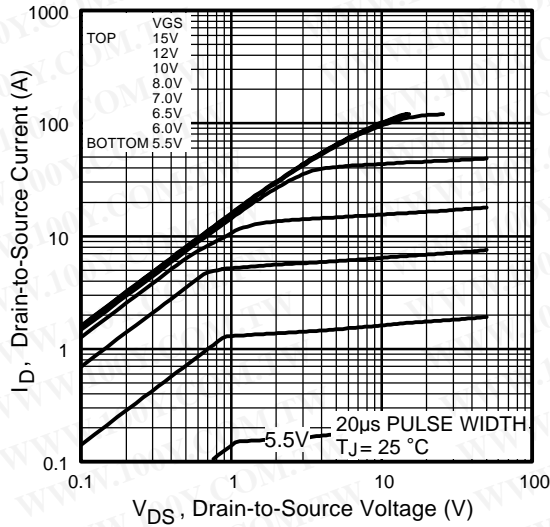
	Parameter	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case	—	0.75	°C/W
$R_{\theta CS}$	Case-to-Sink, Flat, Greased Surface ⑥	0.50	—	
$R_{\theta JA}$	Junction-to-Ambient⑦	—	62	
$R_{\theta JA}$	Junction-to-Ambient⑦	—	40	

## Diode Characteristics

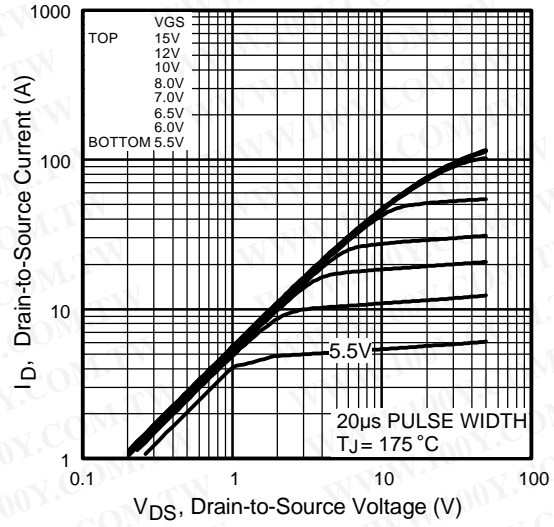
	Parameter	Min.	Typ.	Max.	Units	Conditions
$I_S$	Continuous Source Current (Body Diode)	—	—	31	A	MOSFET symbol showing the integral reverse p-n junction diode. 
$I_{SM}$	Pulsed Source Current (Body Diode) ①	—	—	124		
$V_{SD}$	Diode Forward Voltage	—	—	1.3	V	$T_J = 25^\circ\text{C}, I_S = 18A, V_{GS} = 0V$ ④
$t_{rr}$	Reverse Recovery Time	—	200	300	ns	$T_J = 25^\circ\text{C}, I_F = 18A$
$Q_{rr}$	Reverse Recovery Charge	—	1.7	2.6	$\mu C$	$di/dt = 100A/\mu s$ ④
$t_{on}$	Forward Turn-On Time	Intrinsic turn-on time is negligible (turn-on is dominated by $L_S + L_D$ )				

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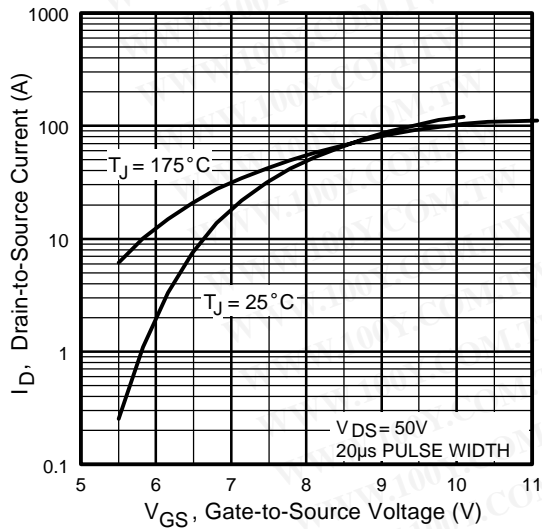
# IRFB/IRFS/IRFSL31N20D



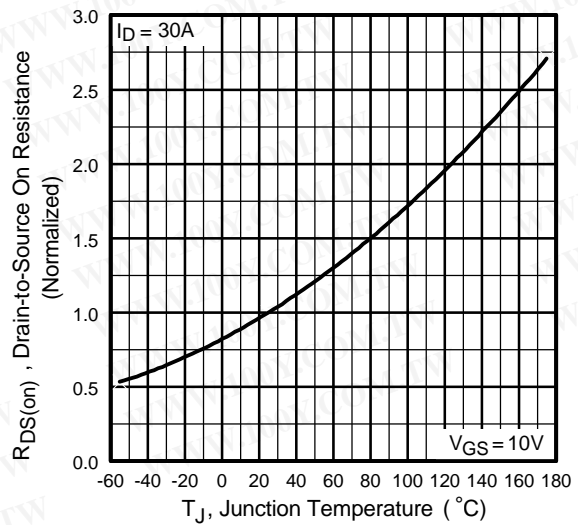
**Fig 1.** Typical Output Characteristics



**Fig 2.** Typical Output Characteristics



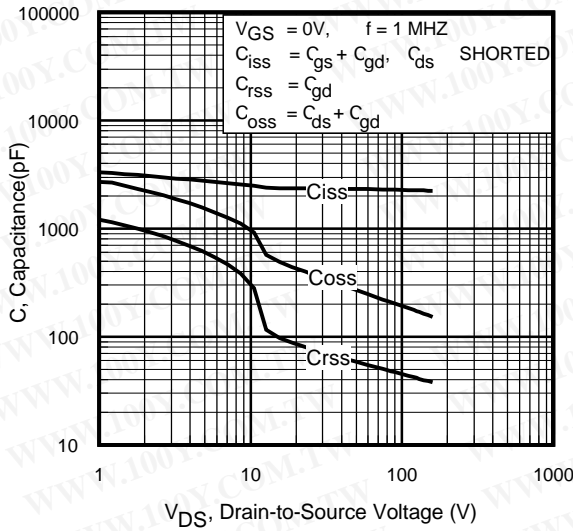
**Fig 3.** Typical Transfer Characteristics



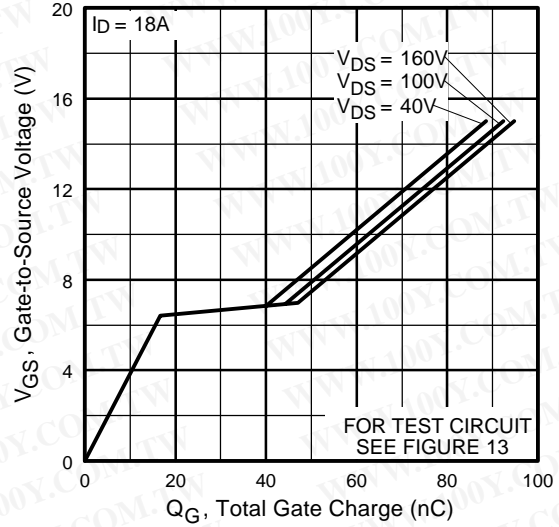
**Fig 4.** Normalized On-Resistance Vs. Temperature

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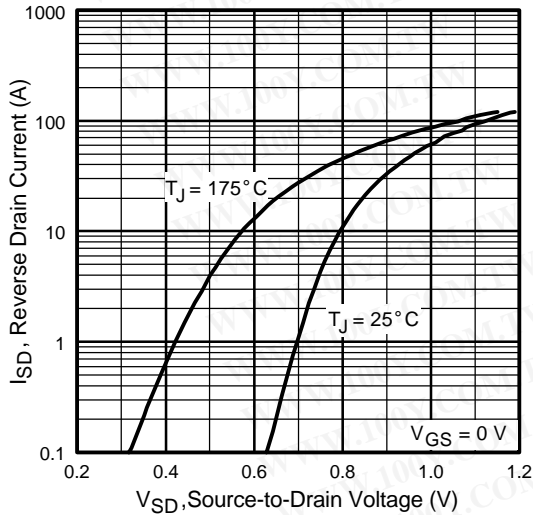
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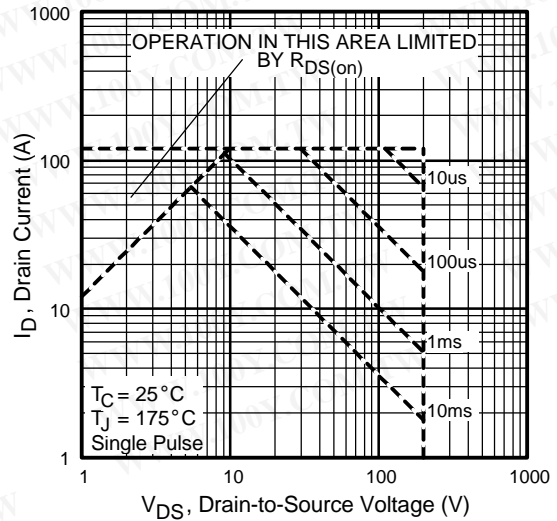
**Fig 5.** Typical Capacitance Vs. Drain-to-Source Voltage



**Fig 6.** Typical Gate Charge Vs. Gate-to-Source Voltage



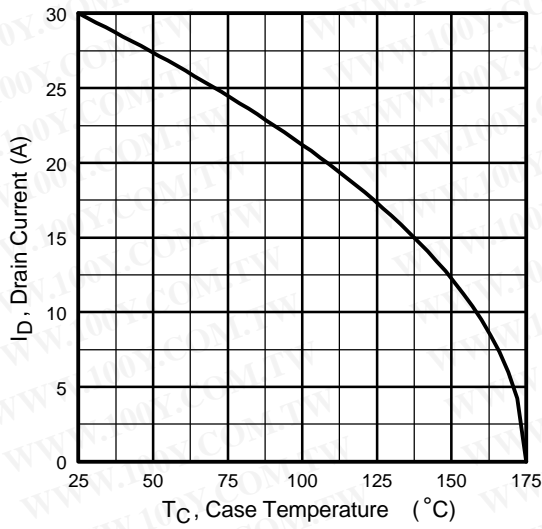
**Fig 7.** Typical Source-Drain Diode Forward Voltage



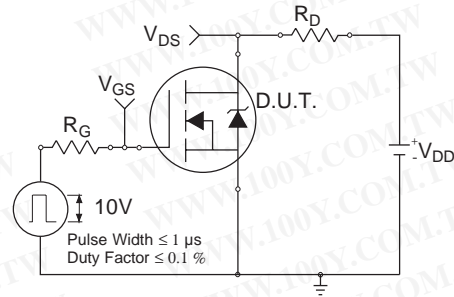
**Fig 8.** Maximum Safe Operating Area

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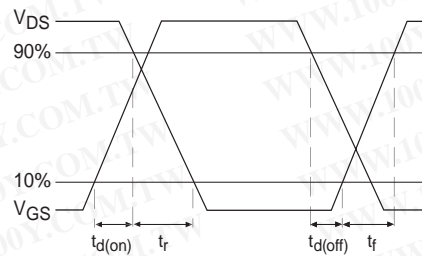
# IRFB/IRFS/IRFSL31N20D



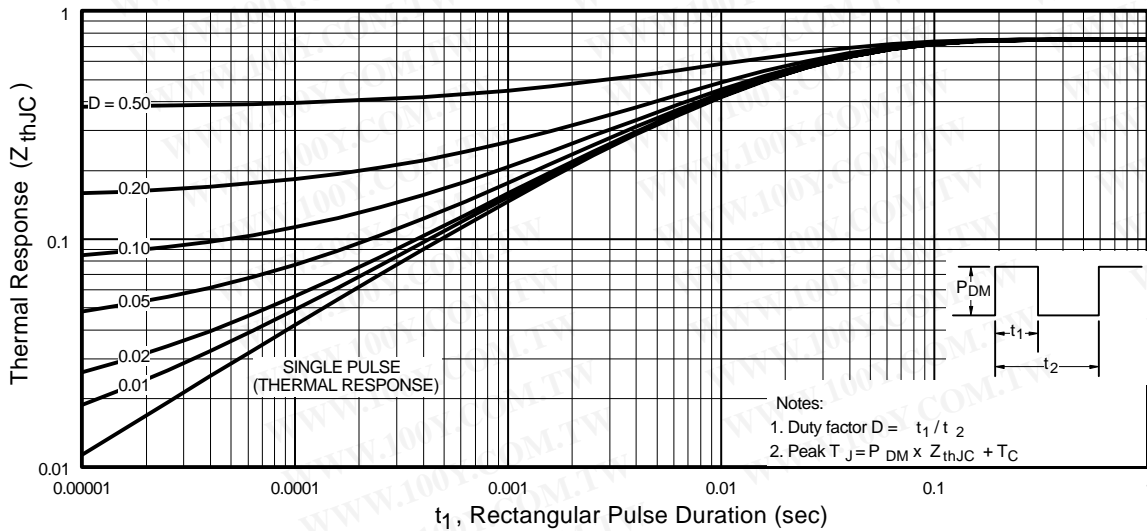
**Fig 9.** Maximum Drain Current Vs. Case Temperature



**Fig 10a.** Switching Time Test Circuit



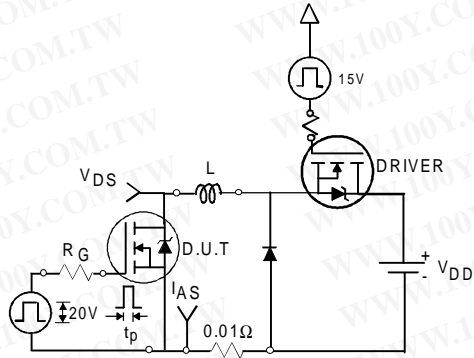
**Fig 10b.** Switching Time Waveforms



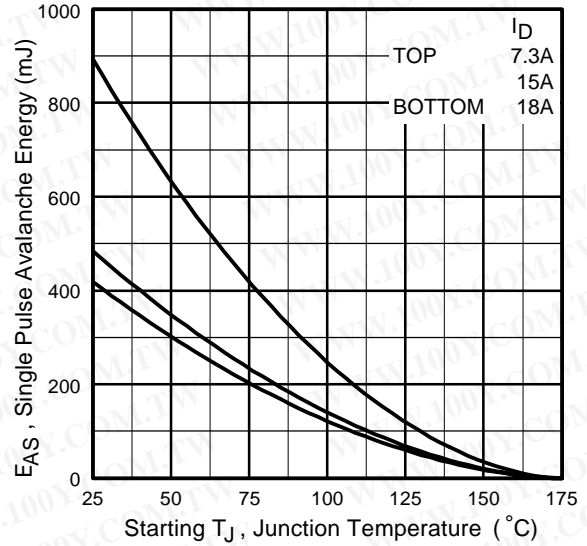
**Fig 11.** Maximum Effective Transient Thermal Impedance, Junction-to-Case

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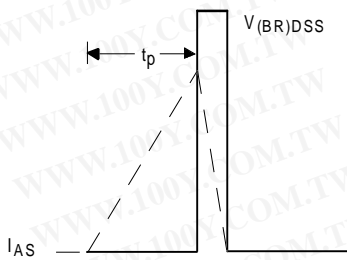
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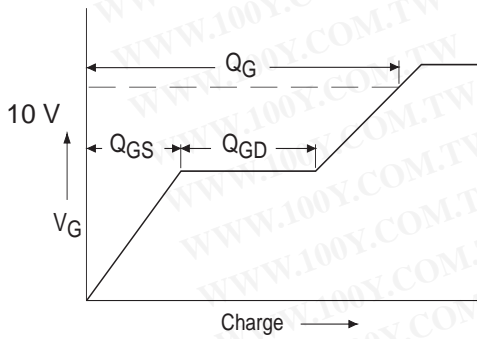
**Fig 12a.** Unclamped Inductive Test Circuit



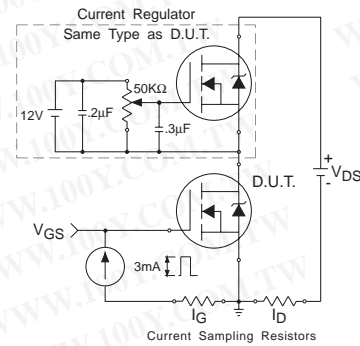
**Fig 12c.** Maximum Avalanche Energy Vs. Drain Current



**Fig 12b.** Unclamped Inductive Waveforms



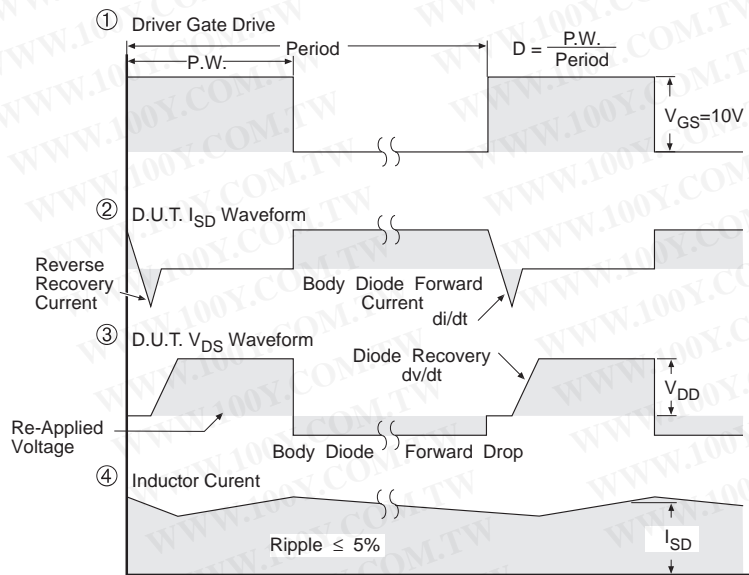
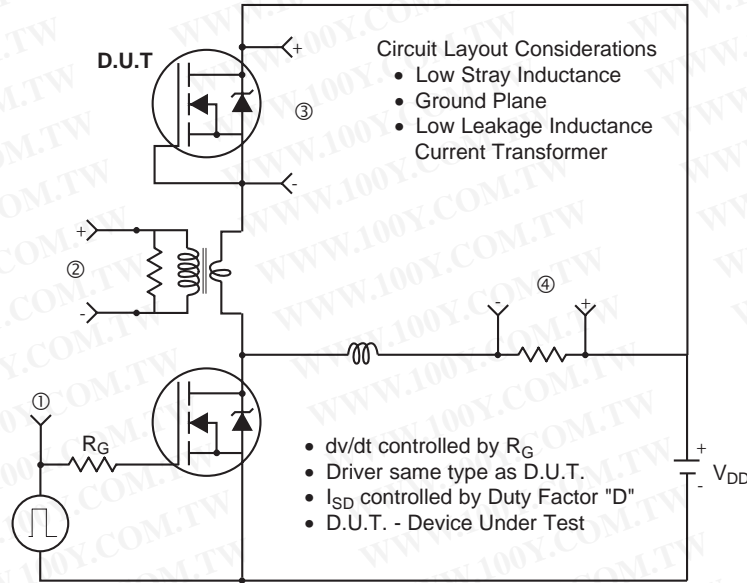
**Fig 13a.** Basic Gate Charge Waveform



**Fig 13b.** Gate Charge Test Circuit

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## Peak Diode Recovery dv/dt Test Circuit



\*  $V_{GS} = 5V$  for Logic Level Devices

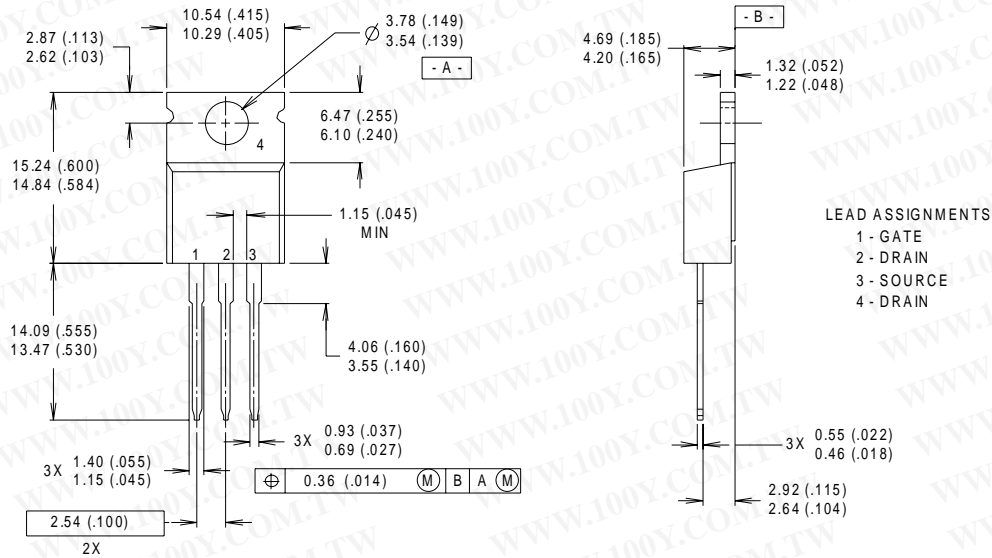
**Fig 14.** For N-channel HEXFET® Power MOSFETs

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## TO-220AB Package Outline

Dimensions are shown in millimeters (inches)

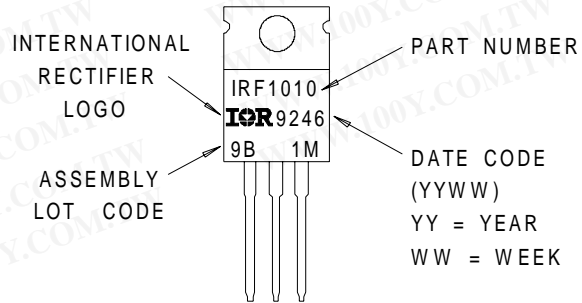


**NOTES:**

- 1 DIMENSIONING & TOLERANCING PER ANSI Y14.5M, 1982.
- 2 CONTROLLING DIMENSION : INCH
- 3 OUTLINE CONFORMS TO JEDEC OUTLINE TO-220AB.
- 4 HEATSINK & LEAD MEASUREMENTS DO NOT INCLUDE BURRS.

## TO-220AB Part Marking Information

EXAMPLE : THIS IS AN IRF1010  
WITH ASSEMBLY  
LOT CODE 9B1M

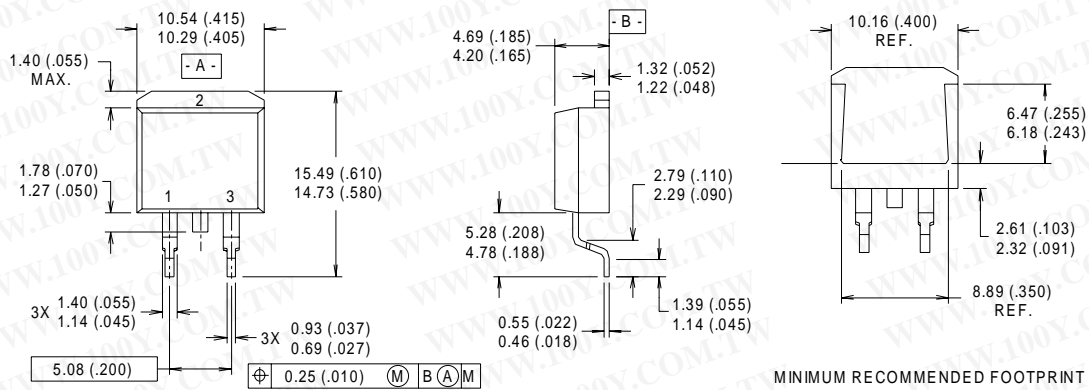




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## D<sup>2</sup>Pak Package Outline



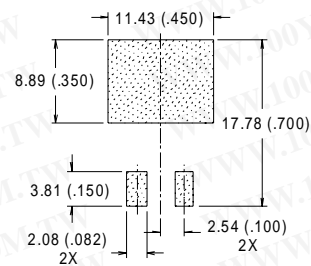
**NOTES:**

- 1 DIMENSIONS AFTER SOLDER DIP.
- 2 DIMENSIONING & TOLERANCING PER ANS IY14.5M, 1982.
- 3 CONTROLLING DIMENSION : INCH.
- 4 HEATSINK & LEAD DIMENSIONS DO NOT INCLUDE BURRS.

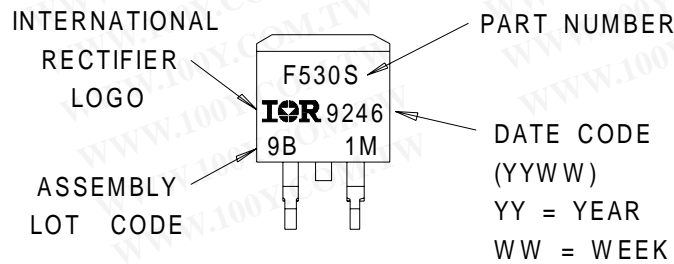
**LEAD ASSIGNMENTS**

- 1 - GATE
- 2 - DRAIN
- 3 - SOURCE

**MINIMUM RECOMMENDED FOOTPRINT**



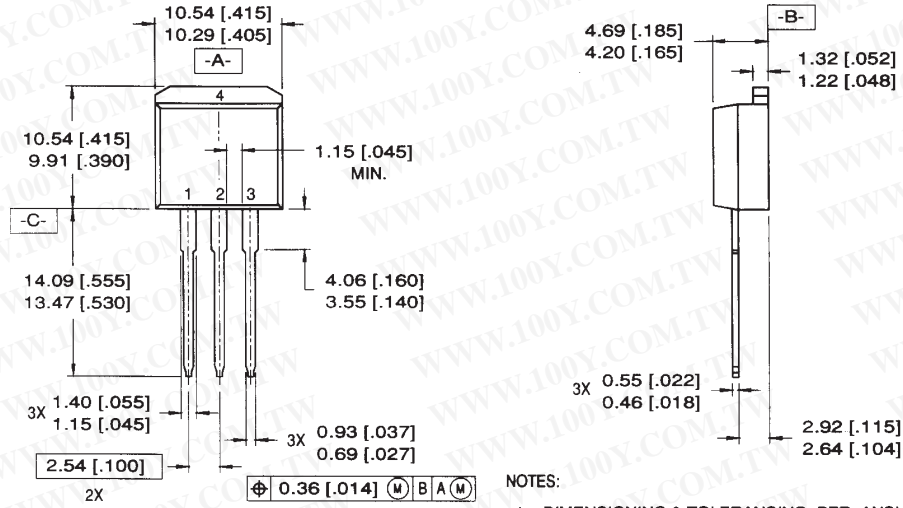
## D<sup>2</sup>Pak Part Marking Information



# IRFB/IRFS/IRFSL31N20D

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**IR** Rectifier

## TO-262 Package Outline



### LEAD ASSIGNMENTS

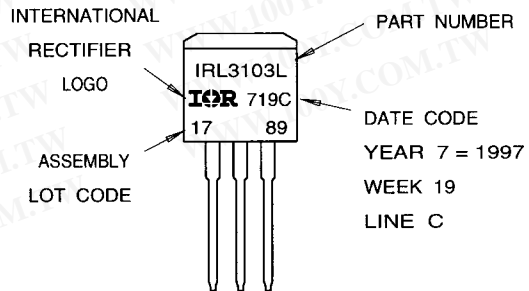
- |           |            |
|-----------|------------|
| 1 = GATE  | 3 = SOURCE |
| 2 = DRAIN | 4 = DRAIN  |

### NOTES:

1. DIMENSIONING & TOLERANCING PER ANSI Y14.5M-1982
2. CONTROLLING DIMENSION: INCH.
3. DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES].
4. HEATSINK & LEAD DIMENSIONS DO NOT INCLUDE BURRS.

## TO-262 Part Marking Information

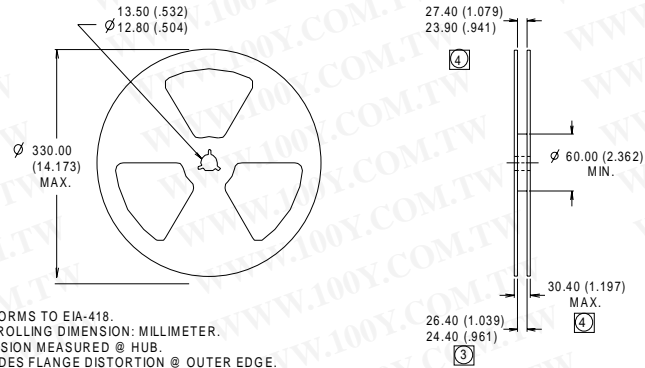
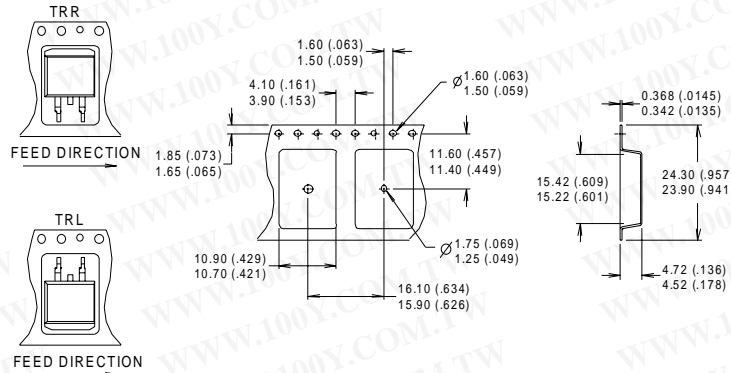
EXAMPLE: THIS IS AN IRL3103L  
 LOT CODE 1789  
 ASSEMBLED ON WW 19, 1997  
 IN THE ASSEMBLY LINE "C"



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## D<sup>2</sup>Pak Tape & Reel Information



- NOTES:
1. CONFORMS TO EIA-418.
  2. CONTROLLING DIMENSION: MILLIMETER.
  - ③ DIMENSION MEASURED @ HUB.
  - ④ INCLUDES FLANGE DISTORTION @ OUTER EDGE.

⑥ This is only applied to TO-220AB package

⑦ This is applied to D<sup>2</sup>Pak, when mounted on 1" square PCB (FR-4 or G-10 Material).  
 For recommended footprint and soldering techniques refer to application note #AN-994.